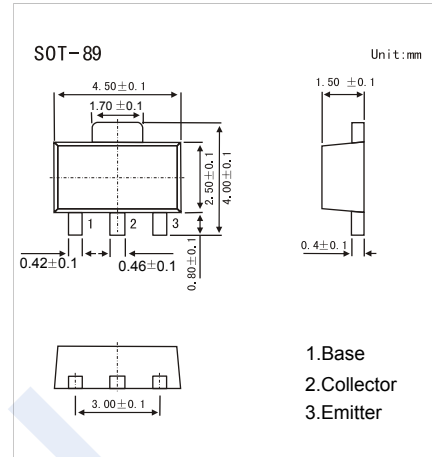


PNP Transistors

2SB1001

■ Features

- Low frequency power amplifier
- Complementary to 2SD1367



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	-20	V
Collector - Emitter Voltage	V _{CEO}	-16	
Emitter - Base Voltage	V _{EBO}	-6	
Collector Current - Continuous	I _C	-2	A
Collector current -Pulse (Note.1)	I _{CP}	-3	
Collector Power Dissipation	P _C	1	W
Junction Temperature	T _J	150	°C
Storage Temperature range	T _{stg}	-55 to 150	

Note.1: PW ≤ 10ms, Duty cycle ≤ 20%

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _C = -100 μA, I _E =0	-20			V
Collector- emitter breakdown voltage	V _{CEO}	I _C = -1 mA, R _{BE} =∞	-16			
Emitter - base breakdown voltage	V _{EBO}	I _E = -100 μA, I _C =0	-6			
Collector-base cut-off current	I _{CB0}	V _{CB} = -16V, I _E =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} = -5V, I _C =0			-0.1	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-1 A, I _B =-100mA		-0.15	-0.3	V
Base - emitter saturation voltage	V _{BE(sat)}	I _C =-1 A, I _B =-100mA		-1	-1.2	
DC current gain	h _{FE}	V _{CE} = -2V, I _C = -100 mA	100		320	
Collector output capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f = 1MHz		50		pF
Transition frequency	f _r	V _{CE} = -2V, I _C = -10mA		150		MHz

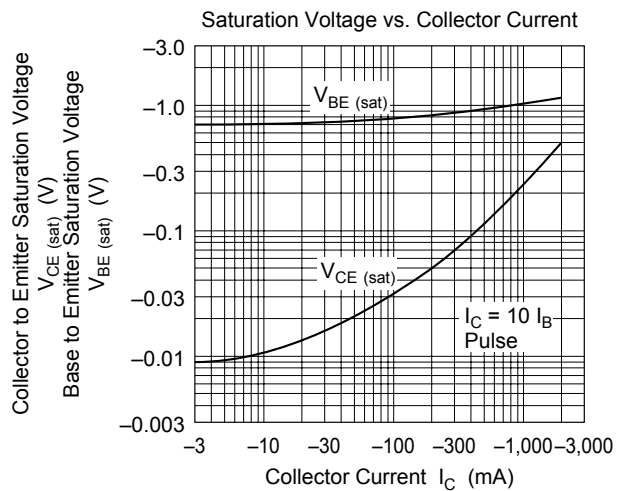
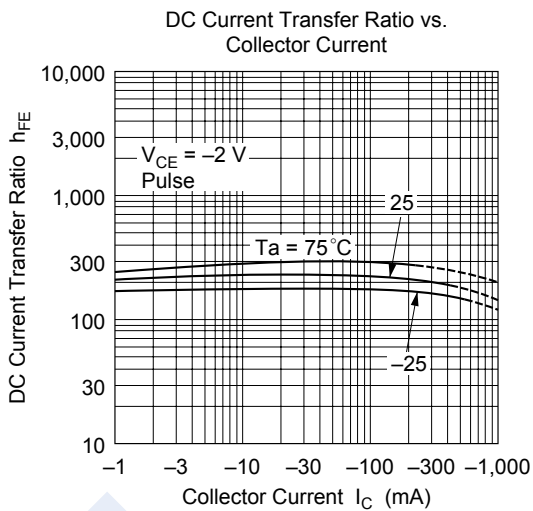
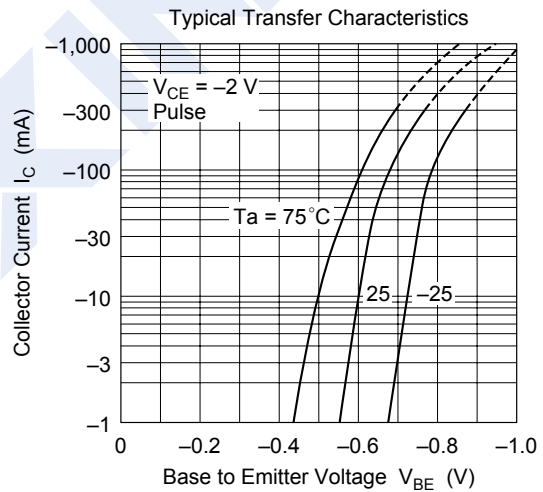
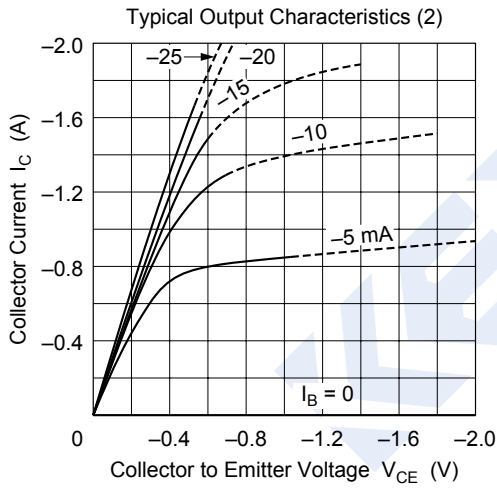
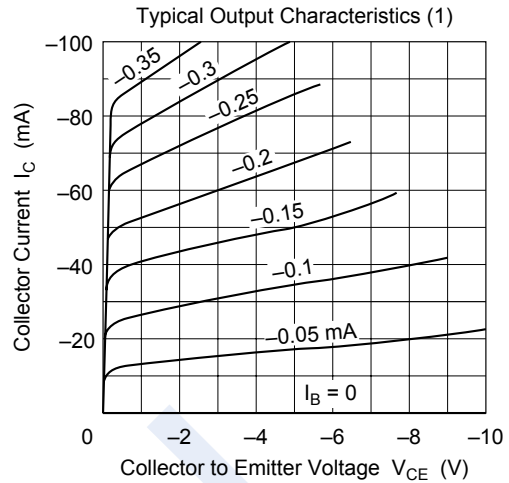
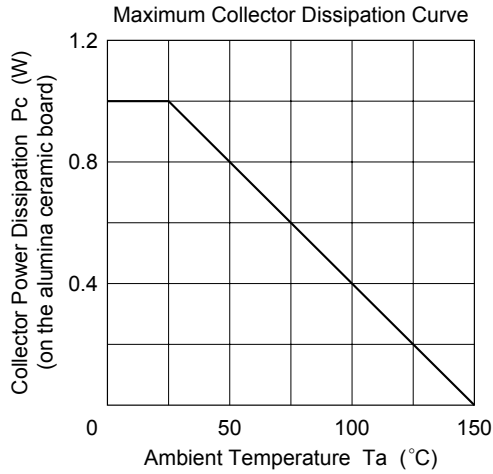
■ Classification of h_{FE}

Type	2SB1001-H	2SB1001-J
Range	100-200	160-320
Marking	BH	BJ

PNP Transistors

2SB1001

Typical Characteristics



PNP Transistors

2SB1001

■ Typical Characteristics

